HARRIS

RFM4N35/4N40
RFP4N35/4N40

N-Channel Enhancement Mode Power Field Effect Transistors

August 1991

Features

- 4A, 350V and 400V
- $r_{DS(on)} = 2\Omega$
- SOA is Power-Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

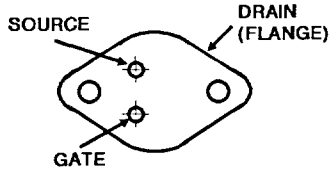
Description

The RFM4N35 and RFM4N40 and the RFP4N35 and RFP4N40 are n-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

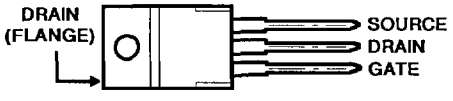
The RFM-series types are supplied in the JEDEC TO-204AA steel package and the RFP-series types in the JEDEC TO-220AB plastic package.

Packages

TO-204AA

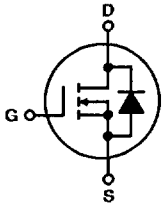


TO-220AB
TOP VIEW



Terminal Diagram

N-CHANNEL ENHANCEMENT MODE



Absolute Maximum Ratings ($T_C = 25^oC$), Unless Otherwise Specified

	RFM4N35	RFM4N40	RFP4N35	RFP4N40	UNITS
Drain-Source Voltage ..... V_{DSS}	350	400	350	400	V
Drain-Gate Voltage ($R_{GS} = 1m\Omega$) ..... V_{DGR}	350	400	350	400	V
Continuous Drain Current					
RMS Continuous ..... I_D	4	4	4	4	A
Pulsed Drain Current ..... I_{DM}	8	8	8	8	A
Gate-Source Voltage ..... V_{GS}	±20	±20	±20	±20	V
Maximum Power Dissipation					
$T_C = +25^oC$ ..... P_D	75	75	60	60	W
Above $T_C = +25^oC$, Derate Linearly	0.6	0.6	0.48	0.48	$W/^oC$
Operating and Storage Junction Temperature Range ..... T_J, T_{STG}	-55 to +150	-55 to +150	-55 to +150	-55 to +150	^oC

CAUTION: These devices are sensitive to electrostatic discharge. Proper I.C. handling procedures should be followed.

File Number **1491.1**

ELECTRICAL CHARACTERISTICS, *At Case Temperature (T_C) 25° C unless otherwise specified.*

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	LIMITS				UNITS
			RFM4N35 RFP4N35		RFM4N40 RFP4N40		
			MIN.	MAX.	MIN.	MAX.	
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=1 mA V_{GS}=0	350	—	400	—	V
Gate Threshold Voltage	$V_{GS}(th)$	V_{GS}=V_{DS} I_D=1 mA	2	4	2	4	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=280 V V_{DS}=320 V	— —	10 —	— —	— 10	μA
		T_C=125° C V_{DS}=280 V V_{DS}=320 V	— —	100 —	— —	— 100	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20 V V_{DS}=0	—	100	—	100	nA
Drain-Source On Voltage	$V_{DS}(on)$[a]	I_D=2 A V_{GS}=10 V	—	4	—	4	V
		I_D=4 A V_{GS}=10 V	—	12	—	12	
Static Drain-Source On Resistance	$r_{DS}(on)$[a]	I_D=2 A V_{GS}=10 V	—	2	—	2	Ω
Forward Transconductance	g_{fs}[a]	V_{DS}=10 V I_D=2 A	1	—	1	—	mho
Input Capacitance	C_{iss}	V_{DS}=25 V V_{GS}=0 V f=1 MHz	—	750	—	750	pF
Output Capacitance	C_{oss}		—	150	—	150	
Reverse Transfer Capacitance	C_{rss}		—	100	—	100	
Turn-On Delay Time	$t_d(on)$	V_{DD}=200 V I_D=2 A R_{gen}=R_{gs}=50 Ω V_{GS}=10 V	12(typ)	45	12(typ)	45	ns
Rise Time	t_r		42(typ)	60	42(typ)	60	
Turn-Off Delay Time	$t_d(off)$		130(typ)	200	130(typ)	200	
Fall Time	t_f		62(typ)	100	62(typ)	100	
Thermal Resistance Junction-to-Case	$R\theta_{JC}$	RFM4N35, RFM4N40	—	1.67	—	1.67	°C/W
		RFP4N35, RFP4N40	—	2.083	—	2.083	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS				UNITS
			RFM4N35 RFP4N35		RFM4N40 RFP4N40		
			MIN.	MAX.	MIN.	MAX.	
Diode Forward Voltage	V_{SD} [a]	I_{SD}=2 A	—	1.4	—	1.4	V
Reverse Recovery Time	t_{rr}	I_F=4 A d_{IF}/d_t=100 A/μs	800(typ)		800(typ)		ns

[a]Pulsed: Pulse duration = 300 μs max., duty cycle = 2%.

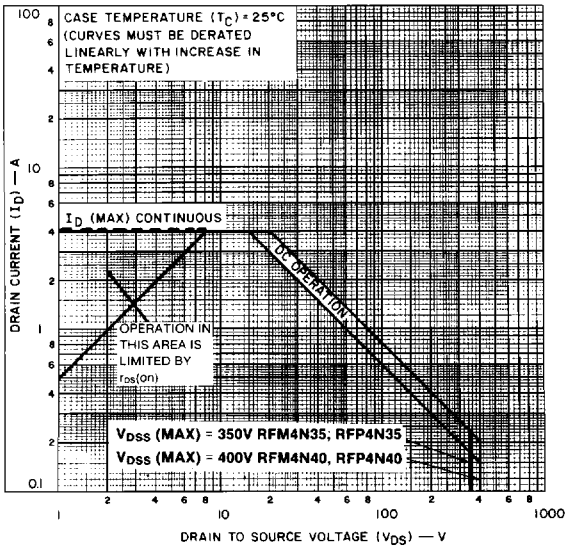


Fig. 1 — Maximum operating areas for all types.

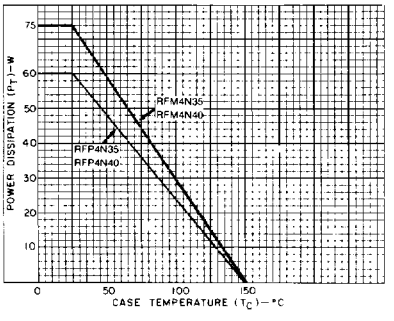


Fig. 2 — Power dissipation vs. temperature derating curve for all types.

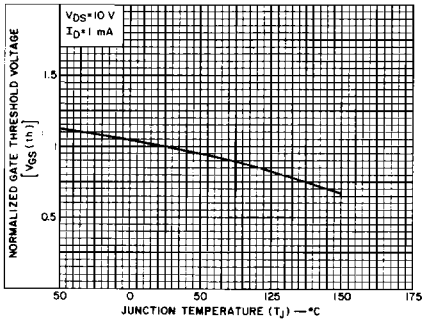


Fig. 3 — Typical normalized gate threshold voltage as a function of junction temperature for all types.

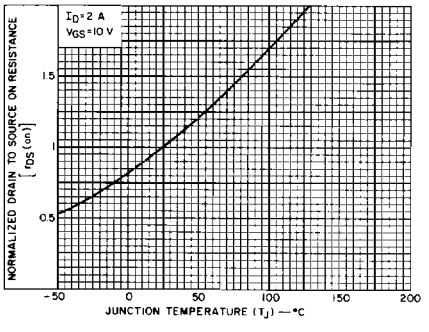


Fig. 4 — Normalized drain-to-source on resistance to junction temperature for all types.

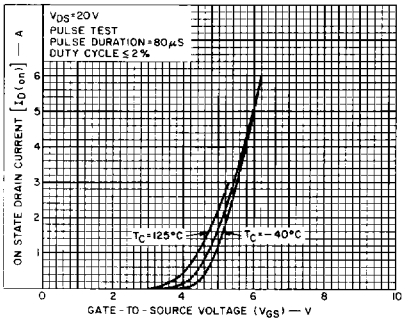


Fig. 5 — Typical transfer characteristics for all types.

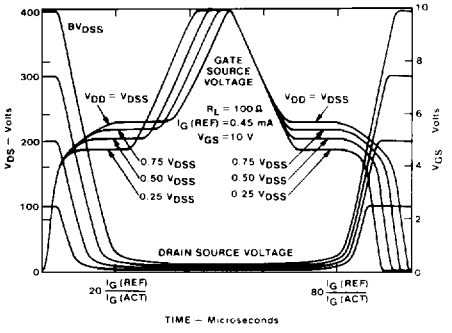


Fig. 6 – Normalized switching waveforms for constant gate-current. Refer to Harris application notes AN-7254 and AN-7260

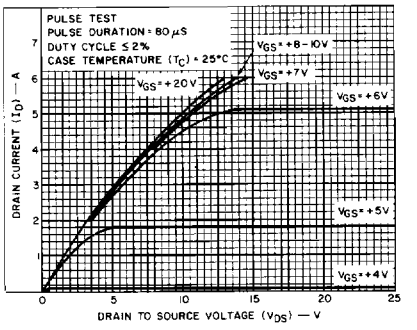


Fig. 7 — Typical saturation characteristics for all types.

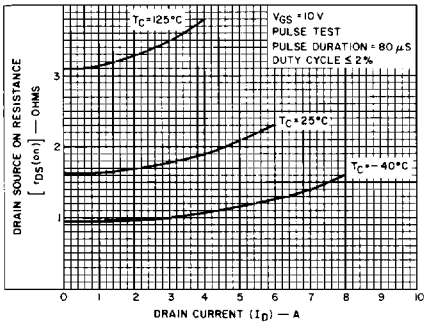


Fig. 8 — Typical drain-to-source on resistance as a function of drain current for all types.

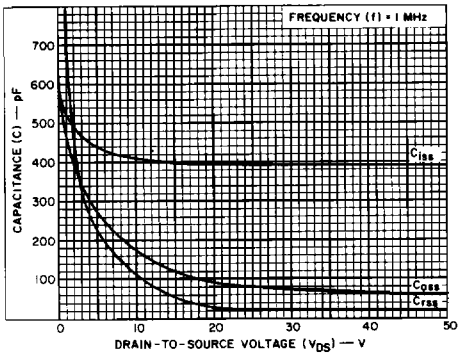


Fig. 9 — Capacitance as a function of drain-to-source voltage for all types.

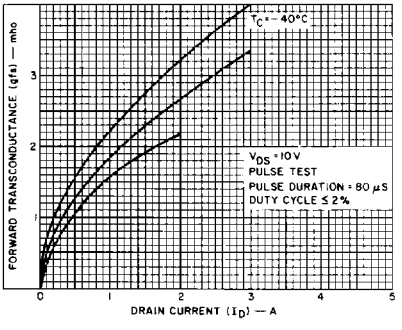


Fig. 10 — Typical forward transconductance as a function of drain current for all types.

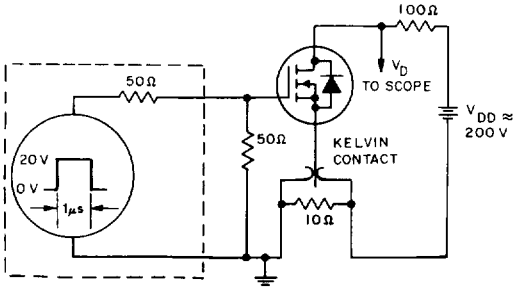


Fig. 11 — Switching Time Test Circuit